SemTron Microtech Corporation

SMC3251SN

Single P-Channel MOSFET

■DESCRIPTION

SMC3251SN is the P-Channel trench technology devices are well suited for high efficiency fast switching applications, low in-line power loss needed in small outline surface mount package.

■FEATURES

V_{DS}=-30V, I_D=-3.7A

$R_{DS(ON)}$=56mΩ(Typ.)@V_{GS}=-10V
$R_{DS(ON)}$=80mΩ(Typ.)@V_{GS}=-4.5V

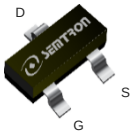
■PART NUMBER INFORMATION

SMC 3251 SN - TR G
a b c d e

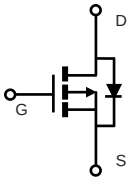
a : Company name.
b : Product Serial number.
c : Package code SN: SOT-23
d : Handling code TR: Tape&Reel
e : Green produce code G: *RoHS Compliant*

■APPLICATIONS

◆Portable Equipment
◆Power Management
◆Load Switch



SOT-23



■ABSOLUTE MAXIMUM RATINGS (T_A=25°C Unless otherwise noted)

Symbol	Parameter		Rating	Units
V_{DSS}	Drain-Source Voltage		-30	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current [A]	T_A=25°C	-3.7	A
		T_A=70°C	-2.9	A
I_{DM}	Pulsed Drain Current [B]		-14.8	A
P_D	Power Dissipation [A]	T_A=25°C	1.3	W
		T_A=70°C	0.8	W
T_J	Operation Junction Temperature		-55/150	°C
T_{STG}	Storage Temperature Range		-55/150	°C

■THERMAL RESISTANCE

Symbol	Parameter		Typ	Max	Units
$R_{\theta JA}$	Thermal Resistance Junction to Ambient [A]	t≦10s		95	°C/W
	Thermal Resistance Junction to Ambient [AC]	Steady-State		130	

■ELECTRICAL CHARACTERISTICS(T_A=25°C Unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Parameters						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=-250μA	-30			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250μA	-1	-1.6	-2	V
I_{GSS}	Gate Leakage Current	V_{DS}=0V, V_{GS}=±20V			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-30V, V_{GS}=0V, T_J=25°C			-1	μA
		V_{DS}=-24V, V_{GS}=0V, T_J=75°C			-10	
$R_{DS(ON)}$	Drain-source On-Resistance [D]	V_{GS}=-10V, I_D=-3.7A V_{GS}=-4.5V, I_D=-2.3A		56 80	65 95	mΩ
G_{fs}	Forward Transconductance	V_{DS}=-10V, I_D=-3.7A		6.5		S
Diode Characteristics						
V_{SD}	Diode Forward Voltage [D]	I_S=-1A,V_{GS}=0V			-1	V
I_S	Diode Continuous Forward Current				-3.7	A
Dynamic and Switching Parameters [E]						
Q_g	Total Gate Charge	V_{DS}=-15V, V_{GS}=-10V I_D =-3.7A		9.8	13.8	nC
Q_g	Total Gate Charge (4.5V)			4.8	6.7	
Q_{gs}	Gate-Source Charge			1.7	2	
Q_{gd}	Gate-Drain Charge			2	2.8	
C_{iss}	Input Capacitance	V_{DS} =-15V,V_{GS} =0V, f =1MHz		510		pF
C_{oss}	Output Capacitance			48		
C_{rss}	Reverse Transfer Capacitance			31		
$t_{d(on)}$	Turn-On Time	V_{DD}=-15V, V_{GEN}=-10V R_G=3.3Ω, I_D=-1A		3.2	6	nS
t_r				9.5	18	
$t_{d(off)}$	Turn-Off Time			16	30	
t_f				5.7	11	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

A. Surface mounted on FR4 board using 1 in^2 pad size.
B. Pulsed width limited by maximum junction temperature, $T_{J(MAX)}$=150°C (initial temperature T_J=25°C).
C. Using ≤ 10s junction-to-ambient thermal resistance is base on $T_{J(MAX)}$=150°C.
D. Pulse test width ≤300μs and duty cycle ≤ 2%.
E. Guaranteed by design, not subject to production testing.

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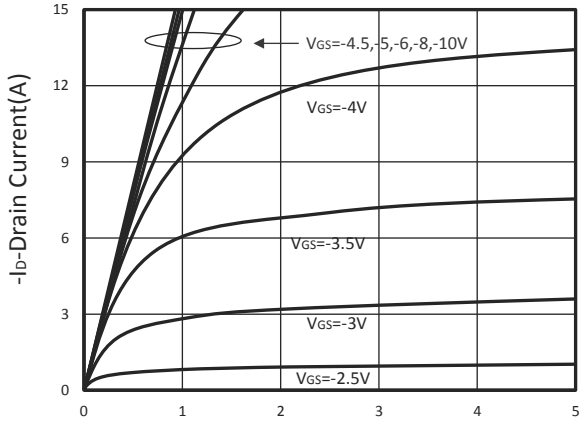
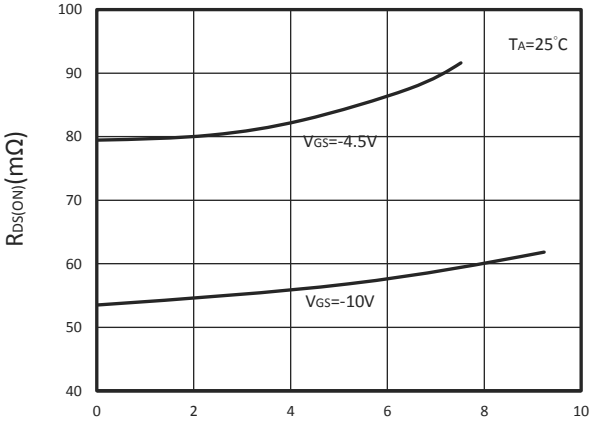
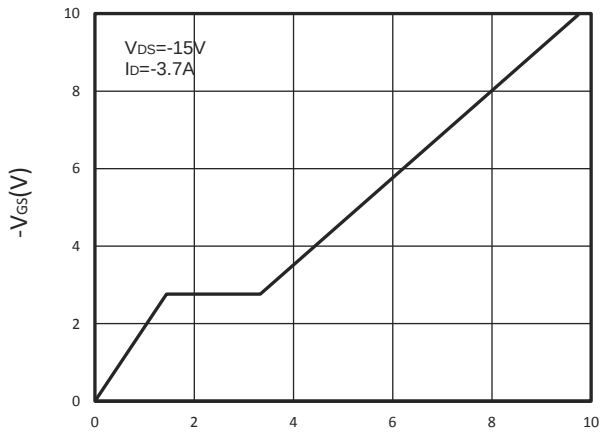
TYPICAL CHARACTERISTICS



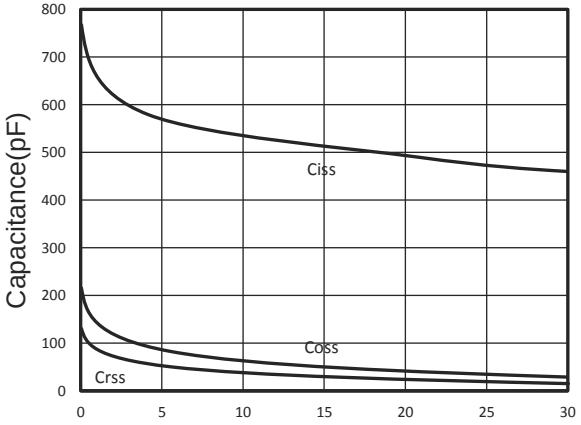
Output Characteristics



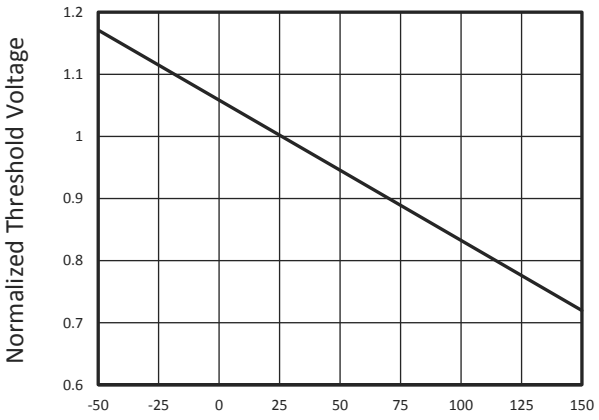
Drain-Source On Resistance



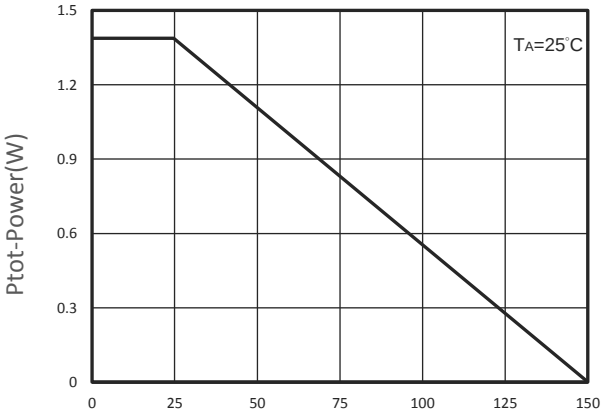
Gate Charge



Capacitance

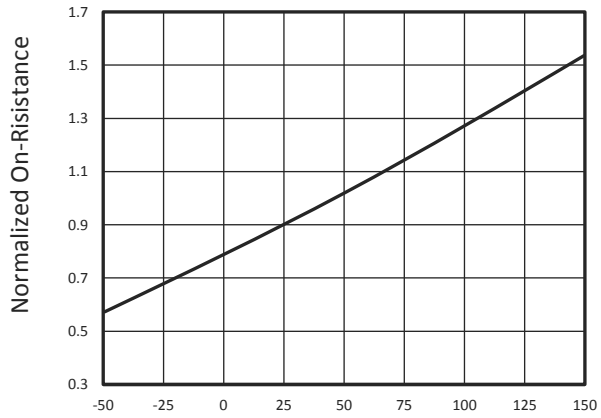


Gate Threshold Voltage



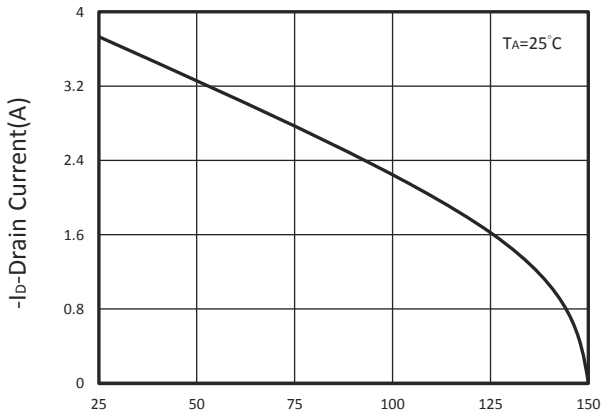
Power Dissipation

TYPICAL CHARACTERISTICS



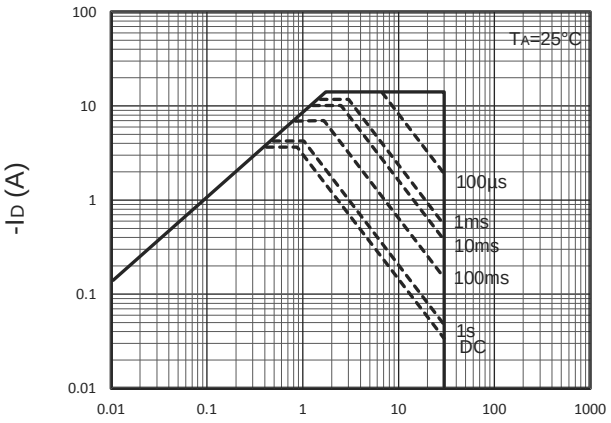
T_J-Junction Temperature(°C)

Drain-Source On Resistance



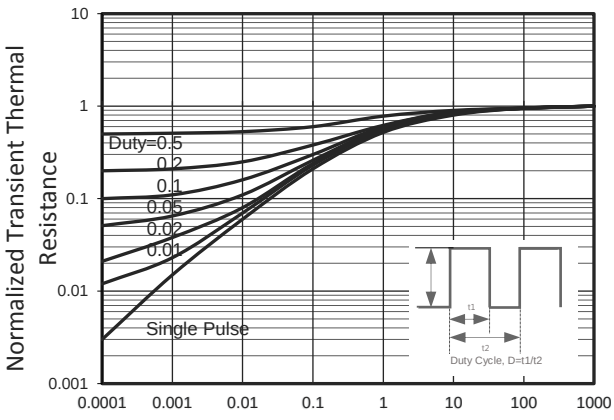
T_J-Junction Temperature(°C)

Drain Current vs T_J



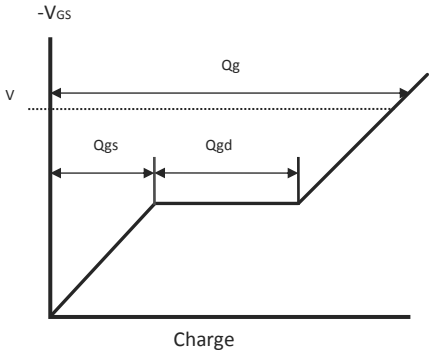
- V_{DS} Voltage (V)

Maximum Safe Operation Area

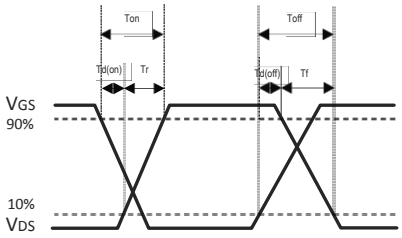


Square Wave Pulse Duration(Sec)

Thermal Transient Impedance

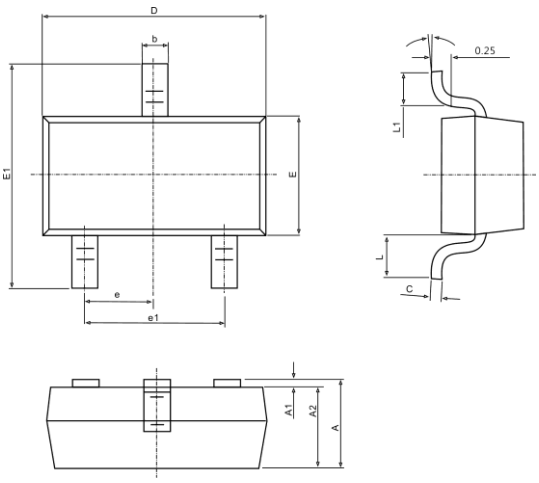


Gate Chrge Waveform

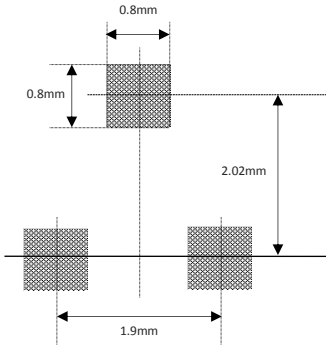


Switching Time Waveform

■SOT-23 PACKAGE DIMENSIONS



Recommended Land Pattern



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.940	1.120	0.037	0.044
A1	0.040	0.120	0.002	0.005
A2	0.900	1.000	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.090	0.110	0.004	0.004
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 BSC		0.037 BSC	
e1	1.800	2.000	0.071	0.079
L	0.500	0.600	0.020	0.024
L	0.550 BSC		0.022 BSC.	
L1	0.300	0.500	0.012	0.020
θ	1°	7°	1°	7°